



### **General Description**

The MAX4806/MAX4807/MAX4808 integrated circuits generate high-voltage, high-frequency, unipolar or bipolar pulses from low-voltage logic inputs. These dual pulsers feature independent logic inputs, independent high-voltage pulser outputs with active clamps, and independent high-voltage supply inputs.

The MAX4806/MAX4807/MAX4808 feature a  $6\Omega$  output impedance for the high-voltage outputs, and a  $20\Omega$ impedance for the active clamp. The high-voltage outputs are guaranteed to provide 2A of output current.

All devices use three logic inputs per channel to control the positive and negative pulses and active clamp. Also included are two independant enable inputs. Disabling EN\_ ensures the output MOSFETs are not accidentally turned on during fast power-supply ramping. This allows for faster ramp times and smaller delays between pulsing modes. A low-power shutdown mode reduces power consumption to less than 1µA. All digital inputs are CMOS compatible.

The MAX4806 includes clamp output overvoltage protection, while the MAX4807 features both pulser output and clamp output overvoltage protection. The MAX4808 does not provide overvoltage protection (see the Ordering Information/Selector Guide).

The MAX4806/MAX4807/MAX4808 are available in a 56-pin (7mm x 7mm), TQFN exposed-pad package and are specified over the 0°C to +70°C commercial temperature range.

**Applications** 

Ultrasound Medical **Imaging** 

**Industrial Sensors** 

Flaw Detection Piezoelectric Drivers Test Instruments

### **Ordering Information**/ Selector Guide

PART	PROTECTED OUTPUTS	OUTPUT CURRENT (A)	PIN- PACKAGE
MAX4806CTN+	OCP_, OCN_	2	56 TQFN-EP**
MAX4807CTN+	OCP_, OCN_, OP_, ON_	2	56 TQFN-EP**
MAX4808CTN+*	None	2	56 TQFN-EP**

**Note:** All devices are specified over the 0°C to +70°C operating temperature range.

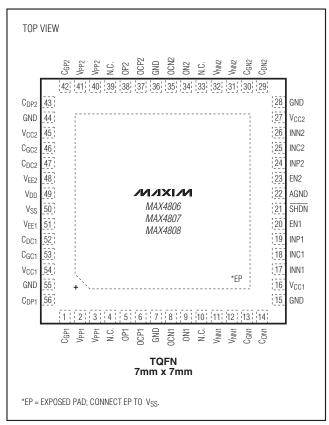
- +Denotes a lead-free/RoHS-compliant package.
- \*Future product. Contact factory for availability.
- \*\*EP = Exposed pad.

Warning: The MAX4806/MAX4807/MAX4808 are designed to operate with high voltages. Exercise caution.

#### **Features**

- ♦ Highly Integrated, High-Voltage, High-Frequency Unipolar/Bipolar Pulser
- ♦ 6Ω Output Impedance and 2A (min) Output Current
- ♦ 20Ω Active Clamp
- **♦** Pulser and Clamp Overvoltage Protection (MAX4806/MAX4807)
- ♦ 0 to +220V Unipolar or ±110V Bipolar Outputs
- ♦ Matched Rise/Fall Times and Matched **Propagation Delays**
- **♦ CMOS-Compatible Logic Inputs**
- ♦ 56-Pin, 7mm x 7mm, TQFN Package

### Pin Configuration



#### **ABSOLUTE MAXIMUM RATINGS**

(Voltages referenced to GND.)	
V <sub>DD</sub> Logic Supply Voltage	0.3V to +6V
V <sub>CC</sub> Output Driver Positive Supply V	oltage0.3V to +15V
VEE Output Driver Negative Supply '	Voltage15V to +0.3V
VPP High Positive Supply Voltage	0.3V to +230V
V <sub>NN</sub> _ High Negative Supply Voltage.	230V to +0.3V
V <sub>SS</sub> Voltage	(Vpp 250V) to V <sub>NN</sub> _
V <sub>PP1</sub> - V <sub>NN1</sub> , V <sub>PP2</sub> - V <sub>NN2</sub> Supply Volt	
INP_, INN_, INC_, EN_, SHDN Logic I	nput0.3V to $(V_{DD} + 0.3V)$
OP_, OCP_, OCN_, ON(-0.3\	<pre>/ + V<sub>NN</sub>) to (-0.3V to V<sub>PP</sub>)</pre>
C <sub>GN</sub> _ Voltage(-0.3V	' + V <sub>NN</sub> _) to (+15V + V <sub>NN</sub> _)
C <sub>GP</sub> _ Voltage(+0.3	3V + V <sub>PP</sub> ) to (-15V + V <sub>PP</sub> )
C <sub>GC_</sub> Voltage	15V to +15V

CDC_, CDP_, CDN_ Voltage	0.3V to V <sub>CC</sub> _
Peak Current per Output Channel	±3.0Ā
Continuous Power Dissipation ( $T_A = +70^{\circ}C$	
56-Pin TQFN (derate 40mW/°C above +	70°C)3200mW
Thermal Resistance (Note 2)	
θυΑ	+25°C/W
θJC	+0.8°C/W
Operating Temperature Range	0°C to +70°C
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

- Note 1: This specification is based on the thermal characteristic of the package, the maximum junction temperature, and the setup described by JEDEC 51. The maximum power dissipation for the MAX4806/MAX4807/MAX4808 might be limited by the thermal protection included in the device.
- **Note 2:** Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to <a href="https://www.maxim-ic.com/thermal-tutorial">www.maxim-ic.com/thermal-tutorial</a>.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{DD} = +2.7V \text{ to } +6V, V_{CC} = +4.75V \text{ to } +12.6V, V_{EE} = -12.6V \text{ to } -4.75V, V_{NN} = -200V \text{ to } 0V, V_{PP} = 0V \text{ to } (V_{NN} + 200V), V_{SS} \le \text{the lower of } V_{NN1} \text{ or } V_{NN2}, T_A = T_J = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$  Typical values are at  $T_A = +25^{\circ}C$ .) (Note 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLY (VDD, VCC_, VE	E_, V <sub>PP</sub> _, V <sub>N</sub>	N_)	•			
Logic Supply Voltage	$V_{DD}$		+2.7	+3	+6	V
Positive Drive Supply Voltage	V <sub>CC</sub> _		+4.75	+12	+12.6	V
Negative Drive Supply Voltage	V <sub>EE</sub> _		-12.6	-12	-4.75	V
High-Side Supply Voltage	V <sub>PP</sub> _		0		V <sub>NN</sub> _ + 220	V
Low-Side Supply Voltage	V <sub>NN</sub> _		-200		0	V
V <sub>PP</sub> V <sub>NN</sub> _ Supply Voltage			0		+220	V
SUPPLY CURRENT (Single Char	nnel)					
		$V_{INN} = V_{INP} = 0, V_{\overline{SHDN}} = 0$			1	
V <sub>DD</sub> Supply Current	I <sub>DD</sub>	V <sub>EN_</sub> = V <sub>DD</sub> , V <sub>SHDN</sub> = V <sub>DD</sub> , V <sub>INC_</sub> = 0 or V <sub>DD</sub> , V <sub>INN_</sub> = V <sub>INP_</sub> , f = 5MHz		100	350	μΑ
		V <sub>SHDN</sub> = 0, channel 1 and channel 2			1	
		V <sub>EN_</sub> = V <sub>DD</sub> , V <sub>SHDN</sub> = V <sub>DD</sub> , channel 1 and channel 2		130	200	μΑ
V <sub>CC</sub> _ Supply Current	ICC_	V <sub>EN_</sub> = V <sub>DD</sub> , V <sub>SHDN</sub> = V <sub>DD</sub> , V <sub>INC_</sub> = 0 or V <sub>DD</sub> , V <sub>INN_</sub> = V <sub>INP_</sub> , f = 5MHz, V <sub>CC</sub> = 5V, V <sub>DD</sub> = 3V, only one channel switching		18		A
		$V_{EN} = V_{DD}$ , $V_{\overline{SHDN}} = V_{DD}$ , $V_{INC} = 0$ or $V_{DD}$ , $V_{INN} = V_{INP}$ , $f = 5MHz$ , $V_{CC} = 12V$ , $V_{DD} = 3V$ , only one channel switching		44		mA

### **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = +2.7 \text{V to } +6 \text{V}, V_{CC}\_ = +4.75 \text{V to } +12.6 \text{V}, V_{EE}\_ = -12.6 \text{V to } -4.75 \text{V}, V_{NN}\_ = -200 \text{V to } 0 \text{V}, V_{PP}\_ = 0 \text{V to } (V_{NN}\_ + 200 \text{V}), V_{SS} \leq \text{the lower of } V_{NN1} \text{ or } V_{NN2}, T_A = T_J = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } T_A = +25 ^{\circ}\text{C.}) \text{ (Note 3)}$ 

PARAMETER	PARAMETER SYMBOL CONDITIONS					UNITS	
		VSHDN = 0, channel 1 and channel 2			1		
		V <sub>EN_</sub> = V <sub>DD</sub> , V <del>SHDN</del> = V <sub>DD</sub> , channel 1 and channel 2			1		
V <sub>EE</sub> _Supply Current	IEE_	$V_{EN\_} = V_{DD}$ , $V_{\overline{SHDN}} = V_{DD}$ , $V_{INC\_} = 0$ or $V_{DD}$ , $V_{INN\_} = V_{INP\_}$ , $f = 5MHz$ , $V_{EE\_} = -5V$ , only 1 channel switching			200	μΑ	
		VEN_ = VDD, VSHDN = VDD, VINC_ = 0 or VDD, VINN_ = VINP_, f = 5MHz, VEE_ = -12V, only 1 channel switching			200		
		VSHDN = 0, channel 1 and channel 2			1		
		V <sub>EN_</sub> = V <sub>DD</sub> , V <sub>SHDN</sub> = V <sub>DD</sub> , channel 1 and channel 2		90	160	μΑ	
V <sub>PP</sub> _Supply Current	I <sub>PP</sub> _	$V_{EN\_} = V_{DD}, V_{\overline{SHDN}} = V_{DD}, V_{INC\_} = 0 \text{ or } V_{DD}, V_{INN\_} = V_{INP\_}, f = 5MHz, V_{PP\_} = +5V, V_{NN\_} = -5V, no load, only 1 channel switching$		13			
		VEN_ = VDD, VSHDN = VDD, VINC_ = 0 or VDD, VPP_ = +80V, VNN_ = -80V, pulse repetition frequency = 10kHz, f = 10MHz, four periods, no load, only 1 channel switching	0.65			mA	
	INN_	V <sub>SHDN</sub> = 0, channel 1 and channel 2			1		
V <sub>NN</sub> _ Supply Current		$V_{EN} = V_{DD}$ , $V_{\overline{SHDN}} = V_{DD}$ , channel 1 and channel 2		40	80	μΑ	
		VEN_ = VDD, VSHDN = VDD, VINC_ = 0 or VDD, VINN_ = VINP_, f = 5MHz, VNN_ = -5V, VPP_ = +5V, no load, only 1 channel	13				
		VEN_ = VDD, VSHDN = VDD, VINC_ = 0 or VDD, VPP_ = +80V, VNN_ = -80V, pulse repetition frequency = 10kHz, f = 10MHz, four periods, no load, only 1 channel switching		mA			
LOGIC INPUTS (EN_, SHDN, INN	I_, INP_, INC_	)					
Low-Level Input Voltage	V <sub>IL</sub>			C	).25 x V <sub>DD</sub>	V	
High-Level Input Voltage	VIH		0.75 x V <sub>DD</sub>			V	
Logic-Input Capacitance C <sub>IN</sub>				5		рF	
Logic-Input Leakage I <sub>IN</sub>		$V_{IN} = 0$ or $V_{DD}$			±1	μΑ	
OUTPUT (OUT_)					-		
		No load at OUT_	V <sub>NN</sub> _		V <sub>PP</sub> _		
OUT_ Output Voltage Range	Vout_	Unprotected outputs (see the <i>Ordering Information/Selector Guide</i> ), 100mA load	V <sub>NN</sub> _ + V <sub>PP</sub> 1.5 1.5		V		
		Protected outputs (see the <i>Ordering Information/Selector Guide</i> ), 100mA load	V <sub>NN</sub> _ + 2.5		V <sub>PP</sub> 2.5		
Low-Side Small-Signal Output	R <sub>OUT_LS</sub>	IOP_ = -100mA, VCC_ = +12V ±5%, DC-coupled		5	12	Ω	
Impedance (MAX4806)	1 TOUI_LS	$I_{OP}$ = -100mA, $V_{CC}$ = +5V ±5%, DC-coupled		5	12	24	

### **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = +2.7 \text{V to } +6 \text{V}, V_{CC}\_ = +4.75 \text{V to } +12.6 \text{V}, V_{EE}\_ = -12.6 \text{V to } -4.75 \text{V}, V_{NN}\_ = -200 \text{V to } 0 \text{V}, V_{PP}\_ = 0 \text{V to } (V_{NN}\_ + 200 \text{V}), V_{SS} \leq \text{the lower of } V_{NN1} \text{ or } V_{NN2}, T_A = T_J = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } T_A = +25 ^{\circ}\text{C.}) \text{ (Note 3)}$ 

PARAMETER	SYMBOL	CONDITIONS			TYP	MAX	UNITS
Low-Side Small-Signal Output	R <sub>OUT_LS</sub>	IOP_ = -100mA, V <sub>CC</sub> _ = +12V ±5%	6, DC-coupled		6	13	Ω
Impedance (MAX4807)	11001_LS	$I_{OP} = -100 \text{mA}, V_{CC} = +5 \text{V} \pm 5\%$		6	13	52	
High-Side Small-Signal Output	Rout_Hs	IOP_ = -100mA, V <sub>CC</sub> _ = +12V ±5%	6, DC-coupled		6	12	Ω
Impedance (MAX4806)	11001_HS	IOP_ = -100mA, VCC_ = +5V ±5%	, DC-coupled		8	15	52
High-Side Small-Signal Output	Rout_Hs	IOP_ = -100mA, V <sub>CC</sub> _ = +12V ±5%	6, DC-coupled		7	13	Ω
Impedance (MAX4807)	1,001_02	IOP_ = -100mA, VCC_ = +5V ±5%	, DC-coupled		9	17	32
Low-Side Output Current	loL	V <sub>CC</sub> = +12V ±5%, V <sub>OUT</sub> - V <sub>N</sub>	N_ = 100V	2			А
High-Side Output Current	IoH	VCC_ = +12V ±5%, VOUT VPI	⊃_ = 100V	2			А
	_		MAX4806		110		
Off-Output Capacitance	Co(off)	connected together; V <sub>PP</sub> _ = +100V, V <sub>NN</sub> _ = -100V	MAX4807		70		pF
Off-Output Leakage Current	I <sub>LK</sub>	V <sub>NN</sub> = -100V, V <sub>NN</sub> = -100V V <sub>NN</sub> = -100V, V <sub>PP</sub> = 100V, EN OUT = -100V to +100V		-1		+1	μΑ
Low-Side Signal-Clamp Output		I <sub>OCN_</sub> = -30mA, DC-coupled, V <sub>0</sub> ±5%, V <sub>EE_</sub> = -V <sub>CC_</sub>	CC_ = +12V		20	40	
Impedance	RCLS	I <sub>OCN_</sub> = -30mA, DC-coupled, V ±5%, V <sub>EE_</sub> = -V <sub>CC_</sub>	'CC_ = +5V		20	50	Ω
High-Side Signal-Clamp Output	Pour	I <sub>OCP</sub> = -30mA, DC-coupled, V <sub>C</sub> ±5%, V <sub>EE</sub> = -V <sub>CC</sub>		20	40	Ω	
Impedance	RCHS	I <sub>OCP</sub> = -30mA, DC-coupled, V ±5%, V <sub>EE</sub> = -V <sub>CC</sub>		33	50		
Low Side Cate Short Impedance	$V_{CC}$ = +12V ±5%, $V_{EE}$ = - $V_{CC}$ , $I_{CGN}$ = 10mA, $V_{EN}$ = 0		C_, I <sub>CGN</sub> _ =			100	Ω
Low-side date short impedance	Side Gate Short Impedance RLSH VCC_ = +12V ±5%, VEE_ = -VCC_, ICGN_ = 10mA, EN_ = VDD				7.5	10	kΩ
High-Side Gate Short Impedance	RHSH	V <sub>CC</sub> _ = +12V ±5%, V <sub>EE</sub> _ = -V <sub>C</sub> 10mA, V <sub>EN</sub> _ = 0	C_, I <sub>CGN</sub> _ =			100	Ω
Tigir-olde date offort impedance	пнэн	V <sub>CC</sub> _ = +12V ±5%, V <sub>EE</sub> _ = -V <sub>C</sub> 10mA, EN_ = V <sub>DD</sub>	C_, I <sub>CGN</sub> _ =	5	7.5	10	kΩ
THERMAL SHUTDOWN							
Thermal Shutdown	T <sub>SHDN</sub>	Junction temperature rising			+155		°C
Thermal-Shutdown Hysteresis					20		°C
DYNAMIC CHARACTERISTICS (F	$R_L = 100\Omega, C_L$			res 4–7.)			ı
Logic Input to Output Rise Propagation Delay	tpLH	V <sub>CC</sub> _ = +12V, V <sub>PP</sub> _ = +5V, V <sub>NN</sub> _ = -5V, Figure 4			15		ns
Logic Input to Output Fall Propagation Delay	t <sub>PHL</sub>	V <sub>CC</sub> _ = +12V, V <sub>PP</sub> _ = +5V, V <sub>NN</sub> _ = -5V, Figure 4			15		ns
Logic Input to Output Rise Propagation Delay	tpOH	V <sub>CC</sub> _ = +12V, V <sub>PP</sub> _ = +5V, V <sub>NN</sub> _ = -5V, Figure 4			15		ns
Logic Input to Output Fall Propagation Delay	tpOL	V <sub>CC</sub> _ = +12V, V <sub>PP</sub> _ = +5V, V <sub>NN</sub> _ = -5V, Figure 4			15		ns

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#### **ELECTRICAL CHARACTERISTICS (continued)**

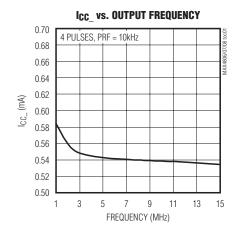
 $(V_{DD} = +2.7 \text{V to } +6 \text{V}, V_{CC}\_ = +4.75 \text{V to } +12.6 \text{V}, V_{EE}\_ = -12.6 \text{V to } -4.75 \text{V}, V_{NN}\_ = -200 \text{V to } 0 \text{V}, V_{PP}\_ = 0 \text{V to } (V_{NN}\_ + 200 \text{V}), V_{SS} \leq \text{the lower of } V_{NN1} \text{ or } V_{NN2}, T_A = T_J = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } T_A = +25 ^{\circ}\text{C.}) \text{ (Note 3)}$ 

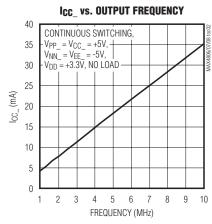
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Logic Input to Output-Rise Propagation Delay Clamp	tPLO	V <sub>CC</sub> = +12V, V <sub>PP</sub> = +5V, V <sub>NN</sub> = -5V, Figure 4		15		ns
Logic Input to Output-Fall Propagation Delay Clamp	tpho	V <sub>CC</sub> _ = +12V, V <sub>PP</sub> _ = +5V, V <sub>NN</sub> _ = -5V, Figure 4		15		ns
OUT_ Rise Time (GND to V <sub>PP</sub> _)	t <sub>ROP</sub>	V <sub>PP</sub> = +100V, V <sub>NN</sub> = -100V, V <sub>CC</sub> = +12V ±5%, V <sub>EE</sub> = - V <sub>CC</sub> , Figure 4			20	ns
OUT_ Rise Time (V <sub>NN</sub> _ to GND)	t <sub>RN0</sub>	V <sub>PP</sub> = +100V, V <sub>NN</sub> = -100V, V <sub>CC</sub> = +12V ±5%, V <sub>EE</sub> = - V <sub>CC</sub> , Figure 4			35	ns
OUT_ Rise Time (V <sub>NN</sub> _ to V <sub>PP</sub> _)	tRNP	V <sub>PP</sub> _ = +100V, V <sub>NN</sub> _ = -100V, V <sub>CC</sub> _ = +12V ±5%, V <sub>EE</sub> _ = - V <sub>CC</sub> _, Figure 4			35	ns
OUT_ Fall Time (GND to V <sub>NN_</sub> )	tFON	V <sub>PP</sub> _ = +100V, V <sub>NN</sub> _ = -100V, V <sub>CC</sub> _ = +12V ±5%, V <sub>EE</sub> _ = - V <sub>CC</sub> _, Figure 4			20	ns
OUT_ Fall Time (VPP_ to GND)	t <sub>FP0</sub>	V <sub>PP</sub> _ = +100V, V <sub>NN</sub> _ = -100V, V <sub>CC</sub> _ = +12V ±5%, V <sub>EE</sub> _ = - V <sub>CC</sub> _, Figure 4			35	ns
OUT_ Fall Time (V <sub>PP</sub> _ to V <sub>NN</sub> _)	tFPN	V <sub>PP</sub> = +100V, V <sub>NN</sub> = -100V, V <sub>CC</sub> = +12V ±5%, V <sub>EE</sub> = - V <sub>CC</sub> , Figure 4			35	ns
OUT_ Enable Time from EN_	t <sub>EN</sub>			100	ns	
(Figure 5)	ιΕΙΛ	V <sub>CC</sub> = +5V ±5%, V <sub>EE</sub> = -V <sub>CC</sub>			150	110
OUT_ Disable Time from EN_	t <sub>DI</sub>	V <sub>CC</sub> = +12V ±5%, V <sub>EE</sub> = -V <sub>CC</sub>			100	ns
(Figure 5)	וטי	V <sub>CC</sub> = +5V ±5%, V <sub>EE</sub> = -V <sub>CC</sub>	0		150	110
Clamp Enable Time from INC_	tEN-CL	$V_{CC}$ = +12V ±5%, $V_{EE}$ = - $V_{CC}$ , Figure 6			150	ns
Clamp Disable Time from INC_	t <sub>DI-CL</sub>	$V_{CC}$ = +12V ±5%, $V_{EE}$ = - $V_{CC}$ , Figure 6		0	150	ns
Short Enable Time from EN_	t <sub>EN_SH</sub>	V <sub>PP</sub> _ = +12V, V <sub>NN</sub> _ = -12V, V <sub>CC</sub> _ = +12V ±5%, V <sub>EE</sub> _ = -V <sub>CC</sub> _, Figure 7			1000	ns
Short Disable Time from EN_	tDI_SH	V <sub>PP</sub> _ = +12V, V <sub>NN</sub> _ = -12V, V <sub>CC</sub> _ = +12V ±5%, V <sub>EE</sub> _ = -V <sub>CC</sub> _, Figure 7			250	ns
Recovery Time from SHDN		V <sub>PP</sub> = +12V, V <sub>NN</sub> = -12V, V <sub>CC</sub> = +12V ±5%, V <sub>EE</sub> = -V <sub>CC</sub>		36.8		ns
Crosstalk		V <sub>PP</sub> = V <sub>CC</sub> = +5V, V <sub>NN</sub> = V <sub>EE</sub> = -5V, f = 5MHz		69		dB
2nd Harmonic Distortion	2HD	V <sub>PP</sub> = +100V, V <sub>NN</sub> = -100V, f <sub>OUT</sub> = 5MHz, V <sub>CC</sub> = +12V		40		dB
RMS Output Jitter	tJ	V <sub>CC</sub> _ = +12V		9		ps

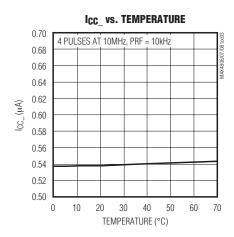
**Note 3:** Specifications are guaranteed for the stated global conditions, unless otherwise noted and are 100% production tested at  $T_A = +25^{\circ}C$  and  $T_A = +70^{\circ}C$ . Specifications at  $T_A = 0^{\circ}C$  are guaranteed by design.

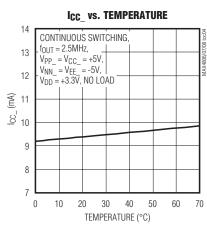
### **Typical Operating Characteristics**

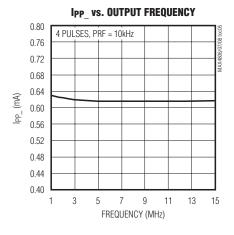
 $(V_{DD} = +3.3V, V_{CC\_} = +12V, V_{EE\_} = -12V, V_{SS} = -100V, V_{PP\_} = +100V, V_{NN\_} = -100V, f_{OUT} = 5MHz, T_{A} = +25^{\circ}C, unless otherwise noted.)$ 

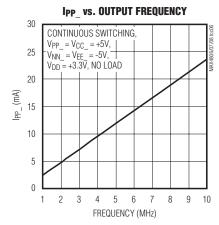


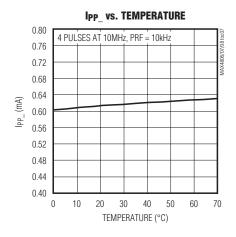


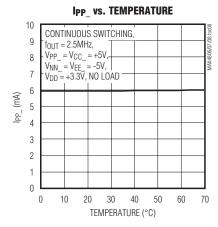


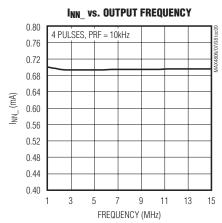






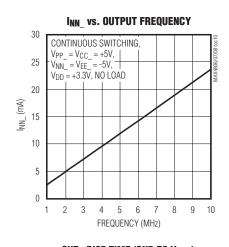


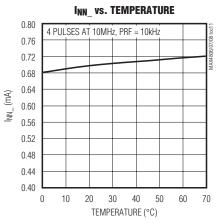


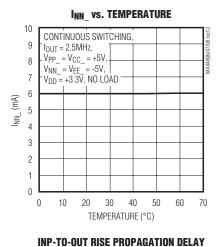


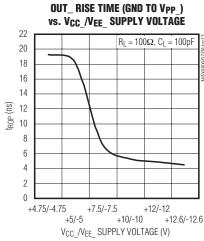
### Typical Operating Characteristics (continued)

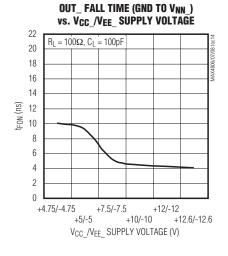
 $(V_{DD} = +3.3V, V_{CC} = +12V, V_{EE} = -12V, V_{SS} = -100V, V_{PP} = +100V, V_{NN} = -100V, f_{OUT} = 5MHz, T_A = +25^{\circ}C$ , unless otherwise noted.)

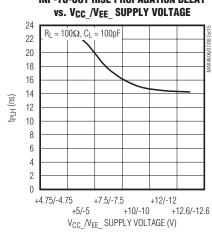


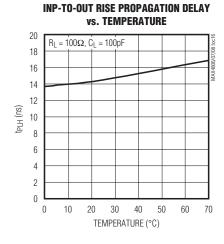


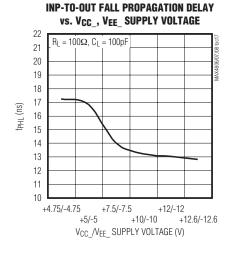


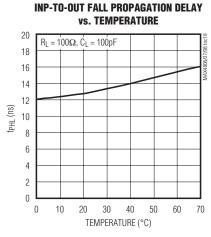












## Pin Description

PIN	NAME	FUNCTION
1	C <sub>GP1</sub>	Channel 1 High-Side Gate Input. Connect a 1nF to 10nF capacitor between C <sub>DP1</sub> and C <sub>GP1</sub> as close as possible to the device.
2, 3	VPP1	Channel 1 High-Side Positive Supply Voltage Input. Bypass V <sub>PP1</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
4, 10, 33, 39	N.C.	No Connection. Not connected internally.
5	OP1	Channel 1 High-Side Drain Output
6	OCP1	Channel 1 High-Side Clamp Output
7, 15, 28, 36, 44, 55	GND	Ground
8	OCN1	Channel 1 Low-Side Clamp Output
9	ON1	Channel 1 Low-Side Drain Output
11, 12	V <sub>NN1</sub>	Channel 1 High-Side Negative Supply Voltage Input. Bypass V <sub>NN1</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
13	C <sub>GN1</sub>	Channel 1 Low-Side Gate Input. Connect a 1nF to 10nF capacitor between C <sub>DN1</sub> and C <sub>GN1</sub> as close as possible to the device.
14	C <sub>DN1</sub>	Channel 1 Low-Side Driver Output. Connect a 1nF to 10nF capacitor between C <sub>DN1</sub> and C <sub>GN1</sub> as close as possible to the device.
16, 54	V <sub>CC1</sub>	Channel 1 Gate-Drive Supply Voltage Input. Bypass V <sub>CC1</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the output, additional bypassing may be required.
17	INN1	Channel 1 Low-Side Logic Input (See Table 1)
18	INC1	Channel 1 Clamp Logic Input. Clamps OCP1 and OCN1 are turned on when INC1 is high and when INP1 and INN1 are low (see Table 1).
19	INP1	Channel 1 High-Side Logic Input (See Table 1)
20	EN1	Channel 1 Enable Logic Input. Drive EN1 high to enable OP1 and ON1. Pull EN1 low to turn on the gate-source short circuit (see Table 1).
21	SHDN	Shutdown Logic Input (See Table 1)
22	AGND	Analog Ground. Must be connected to common GND.
23	EN2	Channel 2 Enable Logic Input. Drive EN2 high to enable OP2 and ON2. Pull EN2 low to turn on the gate-source short circuit (see Table 1).
24	INP2	Channel 2 High-Side Logic Input (See Table 1)
25	INC2	Channel 2 Clamp Logic Input. Clamps OCP2 and OCN2 are turned on when INC2 is high and when INP2 and INN2 are low (see Table 1).
26	INN2	Channel 2 Low-Side Logic Input (See Table 1)
27, 45	V <sub>CC2</sub>	Channel 2 Gate-Drive Supply Voltage Input. Bypass V <sub>CC2</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
29	C <sub>DN2</sub>	Channel 2 Low-Side Driver Output. Connect a 1nF to 10nF capacitor between C <sub>DN2</sub> and C <sub>GN2</sub> as close as possible to the device.
30	C <sub>GN2</sub>	Channel 2 Low-Side Gate Input. Connect a 1nF to 10nF capacitor between C <sub>DN2</sub> and C <sub>GN2</sub> as close as possible to the device.

### Pin Description (continued)

PIN	NAME	FUNCTION
31, 32	V <sub>NN2</sub>	Channel 2 High-Side Negative Supply Voltage Input. Bypass V <sub>NN2</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
34	ON2	Channel 2 Low-Side Drain Output
35	OCN2	Channel 2 Low-Side Clamp Output
37	OCP2	Channel 2 High-Side Clamp Output
38	OP2	Channel 2 High-Side Drain Output
40, 41	V <sub>PP2</sub>	Channel 2 High-Side Positive Supply Voltage Input. Bypass V <sub>PP2</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
42	C <sub>GP2</sub>	Channel 2 High-Side Gate Input. Connect a 1nF to 10nF capacitor between C <sub>DP2</sub> and C <sub>GP2</sub> as close as possible to the device.
43	C <sub>DP2</sub>	Channel 2 High-Side Driver Output. Connect a 1nF to 10nF capacitor between C <sub>DP2</sub> and C <sub>GP2</sub> as close as possible to the device.
46	C <sub>GC2</sub>	Channel 2 High-Side Clamp Gate Input. Connect a 1nF to 10nF capacitor between C <sub>DC2</sub> and C <sub>GC2</sub> as close as possible to the device.
47	C <sub>DC2</sub>	Channel 2 High-Side Clamp Driver Output. Connect a 1nF to 10nF capacitor between C <sub>DC2</sub> and C <sub>GC2</sub> as close as possible to the device.
48	V <sub>EE2</sub>	Channel 2 Negative Supply Input. Gate-drive supply voltage for the OCP2 clamp. Bypass V <sub>EE2</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
49	V <sub>DD</sub>	Logic Supply Voltage Input. Bypass V <sub>DD</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
50	V <sub>SS</sub>	Substrate Voltage. Connect $V_{SS}$ to a voltage equal to or more negative than the more negative of $V_{NN1}$ or $V_{NN2}$ .
51	V <sub>EE1</sub>	Channel 1 Negative Supply Input. Gate-drive supply voltage for the OCP1 clamp. Bypass V <sub>EE1</sub> to GND with a 0.1µF capacitor as close as possible to the device. (See <i>Power Supplies and Bypassing</i> in the <i>Applications Information</i> section.) Depending on the application, additional bypassing may be required.
52	C <sub>DC1</sub>	Channel 1 High-Side Clamp Driver Output. Connect a 1nF to 10nF capacitor between C <sub>DC1</sub> and C <sub>GC1</sub> as close as possible to the device.
53	C <sub>GC1</sub>	Channel 1 High-Side Clamp Gate Input. Connect a 1nF to 10nF capacitor between C <sub>DC1</sub> and C <sub>GC1</sub> as close as possible to the device.
56	C <sub>DP1</sub>	Channel 1 High-Side Driver Output. Connect a 1nF to 10nF capacitor between C <sub>DP1</sub> and C <sub>GP1</sub> as close as possible to the device.
_	EP	Exposed Pad. EP must be connected to VSS. Do not use EP as the only VSS connection for the device.

## **Detailed Description**

The MAX4806/MAX4807/MAX4808 are dual high-voltage, high-speed pulsers that can be independently configured for either unipolar or bipolar pulse outputs. These devices have independent logic inputs for full pulse control and independent active clamps. The clamp input, INC\_, can be set high to activate the clamp automatical-

ly when the device is not pulsing to the positive or negative high-voltage supplies. (See Figures 1, 2, and 3.)

Logic Inputs (INP\_, INN\_, INC\_, EN\_, SHDN)
The MAX4806/MAX4807/MAX4808 have a total of nine logic input signals. SHDN controls power-up and -down of the device. There are two sets of INP\_, INN\_, INC\_ and EN\_ signals: one for each channel. INP\_ controls the

**Table 1. Truth Table** 

	II	NPUTS				OUTPUTS		
SHDN	EN_	INP_	INN_	INC_	OP_	ON_	OCP_, OCN_	STATE
0	Х	Х	Х	0	High Impedance	High Impedance	High Impedance	Powered down, INP_/INN_ disabled, gate-source short disabled
0	Х	Х	Х	1	High Impedance	High Impedance	GND	Powered down, INP_/INN_ disabled, gate-source short disabled
1	0	Х	Х	0	High Impedance	High Impedance	High Impedance	Powered up, INP_/INN_ disabled, gate-source short enabled
1	0	Х	Х	1	High Impedance	High Impedance	GND	Powered up, INP_/INN_ disabled, gate-source short enabled
1	1	0	0	0	High Impedance	High Impedance	High Impedance	Powered up, all inputs enabled, gate-source short disabled
1	1	0	0	1	High Impedance	High Impedance	GND	Powered up, all inputs enabled, gate-source short disabled
1	1	0	1	Х	High Impedance	V <sub>NN</sub> _	High Impedance	Powered up, all inputs enabled, gate-source short disabled
1	1	1	0	Х	V <sub>PP</sub> _	High Impedance	High Impedance	Powered up, all inputs enabled, gate-source short disabled
1	1	1	1	Х	V <sub>PP</sub> _	V <sub>NN</sub> _	High Impedance	Not allowed (3ns maximum overlap)

X = Don't care.

on and off states of the high-side FET, INN\_ controls the on and off states of the low-side FET, INC\_ controls the active clamp, and EN\_ controls the gate-to-source short. These signals give complete control of the output stage of each driver (see Table 1 for all logic combinations).

The MAX4806/MAX4807/MAX4808 logic inputs are CMOS logic compatible, and the logic level is referenced to V<sub>DD</sub> for maximum flexibility. The low 5pF (typ) input capacitance of the logic inputs reduces loading and increases switching speed.

## High-Voltage Output Protection (MAX4807 Only)

The high-voltage outputs of the MAX4807 feature an integrated overvoltage protection circuit that allows the user to implement multilevel pulsing by connecting the outputs of multiple pulser channels in parallel. Internal diodes in series with the ON\_ and OP\_ outputs prevent the body diode of the high-side and low-side FETs from switching on when a voltage greater than V<sub>NN\_</sub> or V<sub>PP\_</sub> is present on the output (see Figure 9).

#### **Active Clamps**

The MAX4806/MAX4807/MAX4808 feature an active clamp circuit to improve pulse quality and reduce 2nd harmonic output. The clamp circuit consists of an nchannel (DC-coupled) and a p-channel (AC and DC delay coupled) high-voltage FETs that are switched on or off by the logic clamp input (INC\_). The MAX4806 and the MAX4807 feature protected clamp devices allowing the clamp circuit to be used in bipolar pulsing circuits (see Figures 1 and 2). A diode in series with the OCN\_ output prevents the body diode of the low-side FET from turning on when a voltage lower than GND is present. Another diode in series with the OCP\_ output prevents the body diode of the high-side FET from turning on when a voltage higher than ground is present. The MAX4808 does not have diode protection on the clamp outputs. Thus, the device is suitable for use in circuits where only unipolar pulsing is required.

The user can connect the active clamp input (INC\_) to a logic-high voltage and drive only the INP\_ and INN\_ inputs to minimize the number of signals used to drive the

\_\_ /N/XI/M

<sup>0 =</sup> Logic-low.

<sup>1 =</sup> Logic-high.

device. In this case, whenever both the INP\_ and INN\_ inputs are low and the INC\_ input is high, the active clamp circuit pulls the output to GND through the OCP\_ and OCN\_ outputs (see Table 1 for more information).

## Power-Supply Ramping and Gate-Source Short Circuit

The MAX4806/MAX4807/MAX4808 include a gate-source short circuit that is controlled by the enable input (EN\_). When  $\overline{SHDN}$  is high and EN\_ is low, a  $60\Omega$  switch shorts together the gate and source of the high-side output FET. At the same time, a similar switch shorts the gate and source of the low-side output FET (Table 1). The gate-source short circuit prevents accidental turn-on of the output FETs due to the ramping voltage on VPP\_ and VNN\_, and allows for faster ramping rates and smaller delay times between pulsing modes.

#### Shutdown Mode

SHDN is common to both channel 1 and channel 2 and powers up or down the device. Drive SHDN low to power down all internal circuits (except the clamp circuits). When SHDN is low, the device is in the lowest power state (1µA) and the gate-source short circuit is disabled. The device takes 36.8ns (typ) to become active when SHDN is disabled.

#### **Thermal Protection**

A thermal-shutdown circuit with a typical threshold of  $+155^{\circ}$ C prevents damage due to excessive power dissipation. When the junction temperature exceeds T<sub>J</sub> =  $+150^{\circ}$ C, all outputs are disabled. Normal operation typically resumes after the IC's junction temperature drops below  $+130^{\circ}$ C.

## Applications Information

#### **AC-Coupling Capacitor Selection**

The value of all AC-coupling capacitors (between Cpp\_ and Cgp\_, and between CpN\_ and CgN\_) should be between 1nF to 10nF. The voltage rating of the capacitor should be greater than  $V_{PP}$  and  $V_{NN}$ . The capacitors should be placed as close as possible to the device.

Because INP\_ and part of INC\_ are AC-coupled to the output devices, they cannot be driven high indefinitely when the device is active.

#### **Power Dissipation**

The power dissipation of the MAX4806/MAX4807/MAX4808 consists of three major components caused by the current consumption from  $V_{CC}$ ,  $V_{PP}$ , and  $V_{NN}$ . The sum of these components ( $P_{VCC}$ ,  $P_{VPP}$ , and  $P_{VNN}$ ) must be kept below the maximum power-dissi-

pation limit. See the *Typical Operating Characteristics* section for more information on typical supply currents versus switching frequencies.

The device consumes most of the supply current from  $V_{CC}$  supply to charge and discharge internal nodes such as the gate capacitance of the high-side FET (Cp) and the low-side FET (C<sub>N</sub>). Neglecting the small quiescent supply current and a small amount of current used to charge and discharge the capacitances at the internal gate clamp FETs, the power consumption can be estimated as follows:

Where f<sub>INN</sub>\_ and f<sub>INP</sub>\_ are the switching frequency of the inputs INN\_ and INP\_ respectively, and where BRF is the Burst Repetition Frequency and BTD is the Burst Time Duration. The typical value gate capacitances of the power FET are  $C_N = 0.3 \mu F$  and  $C_P = 0.6 \mu F$ .

For an output load that has a resistance of  $R_L$  and capacitance of  $C_L$ , the MAX4806/MAX4807/MAX4808 power dissipation can be estimated as follows (assume square-wave output and neglect the resistance of the switches):

$$P_{VPP\_} = \left\{ \! \left[ \left( C_O + C_L \right) \! \times \! \mathfrak{f}_{1N} \! \times \! \left( V_{PP\_} - V_{NN\_} \right)^2 \right] \! + \! \left[ \frac{V_{PP\_}^2}{R_L} \! \times \! \frac{1}{2} \right] \! \times \! \left( \mathsf{BRF} \! \times \! \mathsf{BTD} \right) \right\}$$

Where C<sub>O</sub> is the output capacitance of the device.

#### **Power Supplies and Bypassing**

The MAX4806/MAX4807/MAX4808 operate from independent supply voltage sets (only V<sub>DD</sub> and V<sub>SS</sub> are common to both channels). The logic input circuit operates from a +2.7V to +6V single supply (V<sub>DD</sub>). The level-shift driver dual supplies, V<sub>CC</sub>\_/V<sub>EE</sub>\_ operate from  $\pm 4.75V$  to  $\pm 12.6V$ .

The V<sub>PP</sub>\_/V<sub>NN</sub>\_ high-side and low-side supplies are driven from a single positive supply up to +220V, from a single negative supply up to -200V, or from  $\pm 110$ V dual supplies. Either V<sub>PP</sub>\_ or V<sub>NN</sub>\_ can be set at 0V. Bypass each supply input to ground with a 0.1 $\mu$ F capacitor as close as possible to the device.

Depending on the application, additional bypassing may be needed to maintain the input of both V<sub>NN</sub>\_ and V<sub>PP</sub>\_ stable during output transitions. For example, with C<sub>OUT</sub> = 100pF and R<sub>OUT</sub> = 100 $\Omega$  load, the use of an

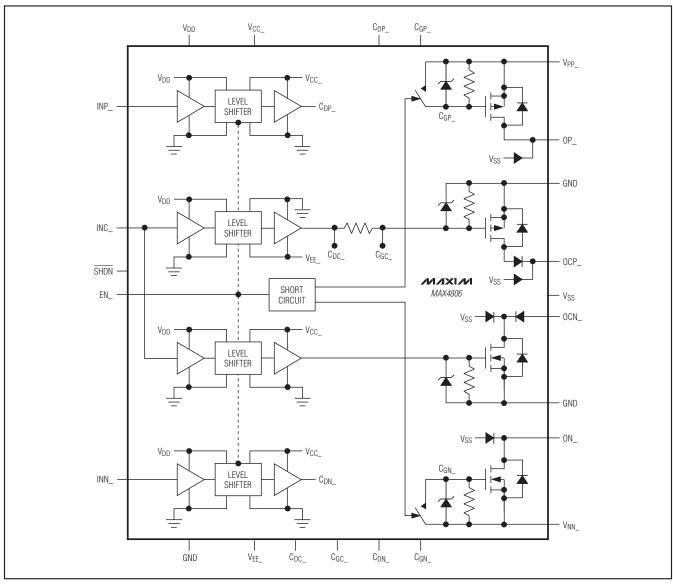


Figure 1. MAX4806 Simplified Functional Diagram for One Channel

additional 10 $\mu$ F (typ) electrolytic capacitor is recommended. VSS is the substrate voltage. Connect VSS to a voltage equal to or more negative than the lower of VNN1 or VNN2.

#### **Exposed Pad and Layout Concerns**

The MAX4806/MAX4807/MAX4808 provide an exposed pad (EP) underneath the TQFN package for improved thermal performance. EP is internally connected to Vss. Connect EP to Vss externally. To aid heat dissipation,

connect EP to a similarly sized pad on the component side of the PCB. This pad should be connected through to the solder-side copper by several plated holes to a large heat-spreading copper area to conduct heat away from the device.

The MAX4806/MAX4807/MAX4808 high-speed pulsers require low-inductance bypass capacitors to their supply inputs. High-speed PCB trace design practices are recommended. Pay particular attention to minimize trace

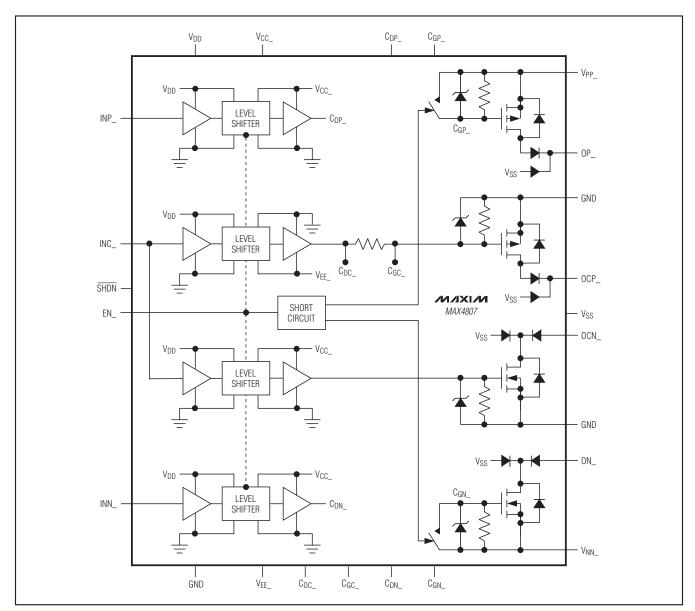


Figure 2. MAX4807 Simplified Functional Diagram for One Channel

lengths and use sufficient trace width to reduce inductance. Use of surface-mount components is recommended.

#### **Supply Sequencing**

Vss must be lower than or equal to the more negative voltage of V<sub>NN1</sub> or V<sub>NN2</sub> at all times, and must be turned on before other supply voltages. No other power-supply sequencing is required for the MAX4806/MAX4807/MAX4808.

#### **Typical Application Circuits**

Figures 8, 9, and 10 show typical applications for the MAX4806/MAX4807/MAX4808. Figure 8 shows the MAX4806 used in a bipolar pulsing connection. Figure 9 shows the MAX4807 in a five-level pulsing application, and Figure 10 shows the MAX4808 used in a unipolar application.

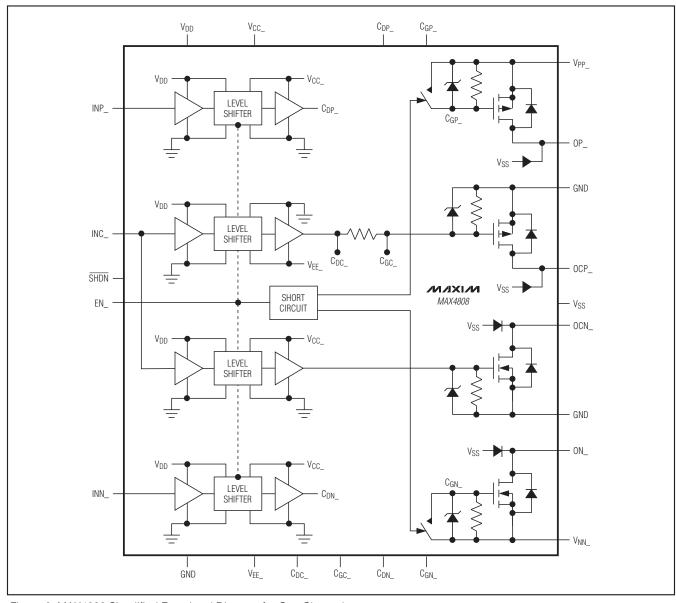


Figure 3. MAX4808 Simplified Functional Diagram for One Channel

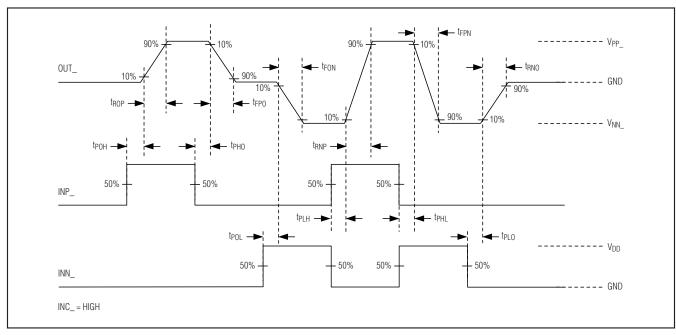


Figure 4. Detailed Timing ( $R_L = 100\Omega$ ,  $C_L = 100pF$ )

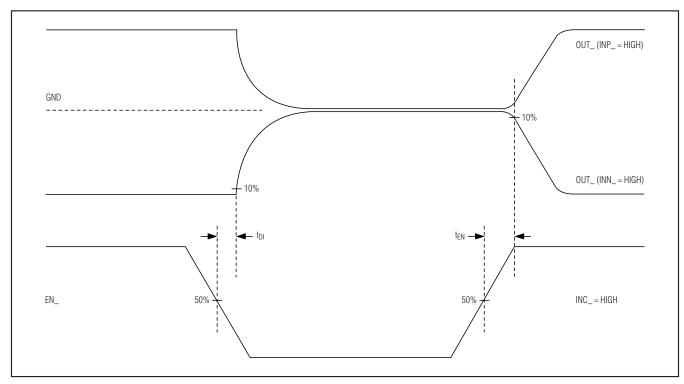


Figure 5. Enable Timing ( $R_L = 100\Omega$ ,  $C_L = 100pF$ )

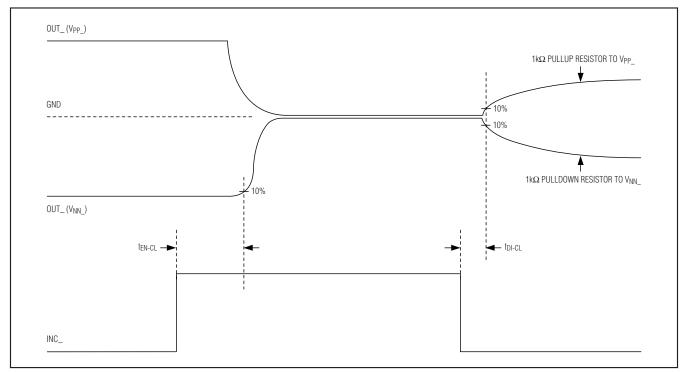


Figure 6. Active Clamp Timing

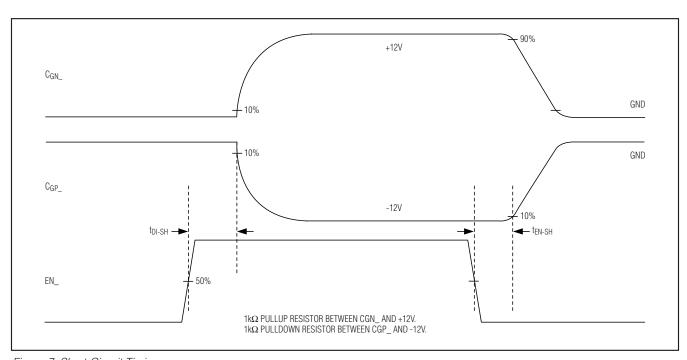


Figure 7. Short-Circuit Timing

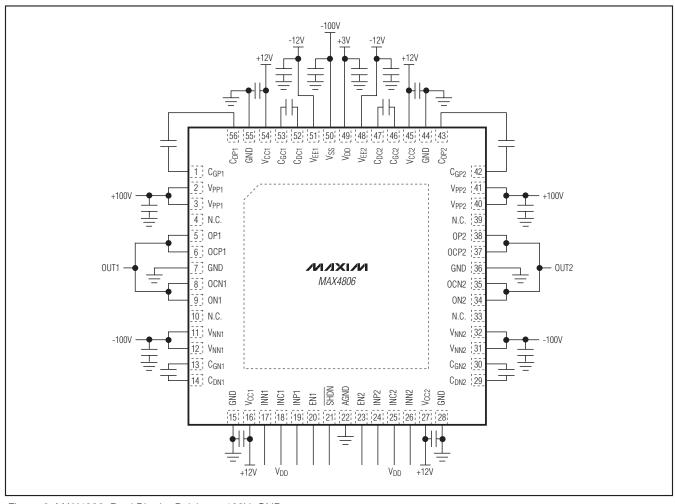


Figure 8. MAX4806: Dual Bipolar Pulsing, ±100V, GND

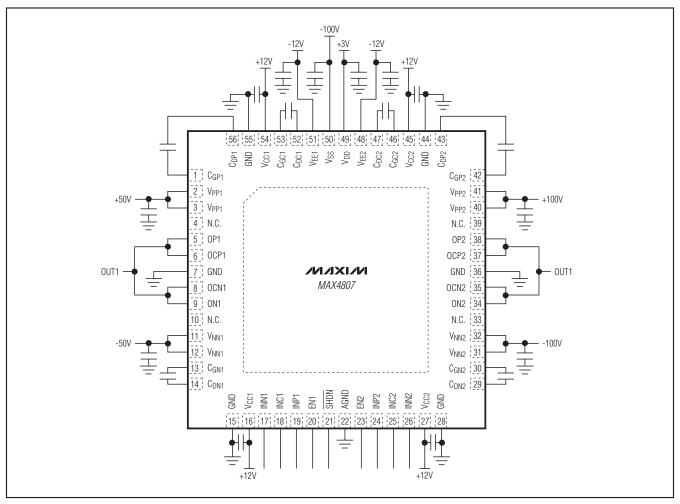


Figure 9. MAX4807: Five-Level Pulsing, ±100V, ±50V, GND

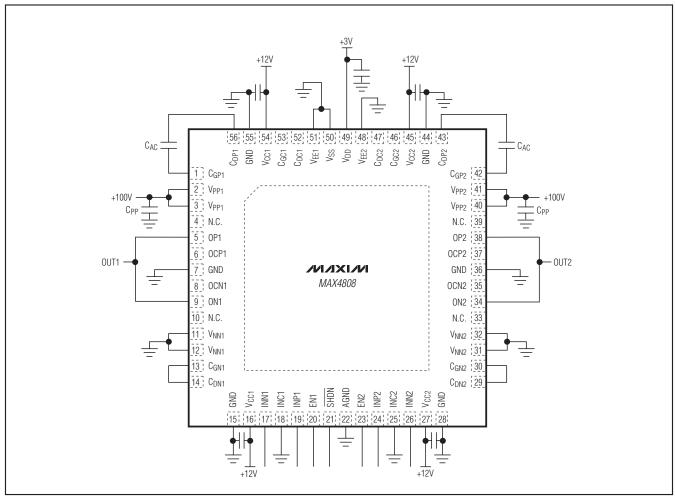


Figure 10. MAX4808: Dual Unipolar Pulsing, +100V, GND

## Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
56 TQFN	T5677-1	<u>21-0144</u>

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